

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	tw-499729-\$.did. tw-445580-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/04/06 08:19
L2	164	((438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and ((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp)) and (ion near implant\$8)) and (sac (aligned adj contact))	US-PGPUB; USPAT	OR	ON	2005/04/06 09:41
L3	1	"6649500".URPN.	USPAT	OR	OFF	2005/04/06 09:56
L4	2	"6268272".URPN.	USPAT	OR	OFF	2005/04/06 09:57
L5	1	"6255206".URPN.	USPAT	OR	OFF	2005/04/06 09:57
L6	172	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) same (ion near implant\$8) same ((contact adj (opening hole via)) plug ((conduct\$6 metal) near via) sac (aligned adj contact)) same (gate source drain) same (sidewall spacer silicide (side adj wall))	US-PGPUB; USPAT	OR	ON	2005/04/06 09:58
L7	206	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and (ion near implant\$8) and ((contact adj (opening hole via)) plug ((conduct\$6 metal) near via)) and (gate source drain sidewall spacer silicide (side adj wall))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/06 10:02
L8	151	(438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and ((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and (((ion near implant\$8) with (argon nitrogen oxygen)) same (gate transistor \$3fet \$1mos (field adj effect)))	US-PGPUB; USPAT	OR	ON	2005/04/06 10:25

L9	98	(438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and (((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) same ((implant\$8 with (argon nitrogen oxygen)) same (gate transistor \$3fet \$1mos (field adj effect))))	US-PGPUB; USPAT	OR	ON	2005/04/06 10:35
L10	154	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) same ((implant\$8 near2 (argon nitrogen oxygen)) with (gate transistor \$3fet \$1mos (field adj effect)))	US-PGPUB; USPAT	OR	ON	2005/04/06 11:29
L11	189	((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp) and ((implant\$8 with (argon nitrogen oxygen)) and (gate transistor \$3fet \$1mos (field adj effect)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/06 11:33
L12	1765	((438/525.ccls. 438/528.ccls. 438/586.ccls. 438/592.ccls. 438/595.ccls. 438/637.ccls. 438/675.ccls. 438/766.ccls. 438/770.ccls.) and ((thermal\$4 near (process\$6 oxid\$8)) (rapid adj thermal) rto rta rtp)) and (ion near implant\$8)	US-PGPUB; USPAT	OR	ON	2005/04/06 11:46